

Silicon PNP Power Transistors

2SA1170

DESCRIPTION

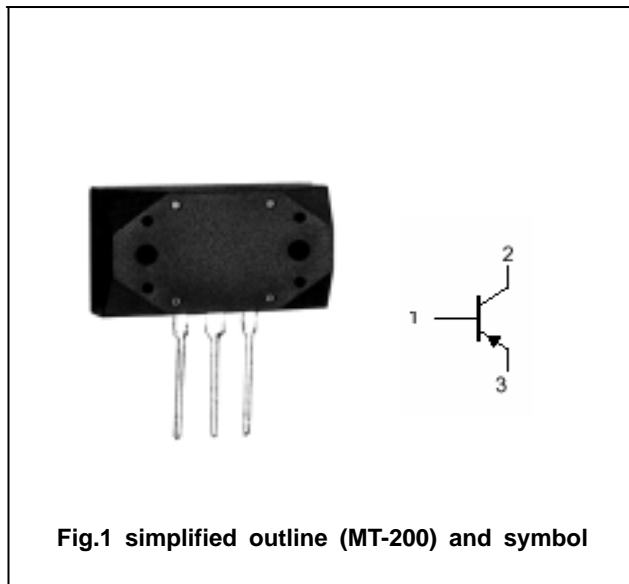
- With MT-200 package
- High power dissipation
- Complement to type 2SC2774

APPLICATIONS

- Audio and general purpose applications

PINNING (see Fig.2)

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-200	V
V _{CEO}	Collector-emitter voltage	Open base	-200	V
V _{EBO}	Emitter-base voltage	Open collector	-6	V
I _C	Collector current		-17	A
I _B	Base current		-5	A
P _C	Collector power dissipation	T _C =25	200	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-50mA ; I _B =0	-200			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-1mA ; I _C =0	-6			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-10A ; I _B =-1A			-2.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-200V ; I _E =0			-100	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =-6V ; I _C =0			-100	μ A
h _{FE}	DC current gain	I _C =-8A ; V _{CE} =-4V	20			
f _T	Transition frequency	I _C =-1A ; V _{CE} =-12V		20		MHz

Switching times

t _r	Rise time	I _C =-10A ; I _{B1} =- I _{B2} =-1A R _L =4 ; V _{CC} =-40V		0.6		μ s
t _{stg}	Storage time			0.9		μ s
t _f	Fall time			0.2		μ s

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PACKAGE OUTLINE

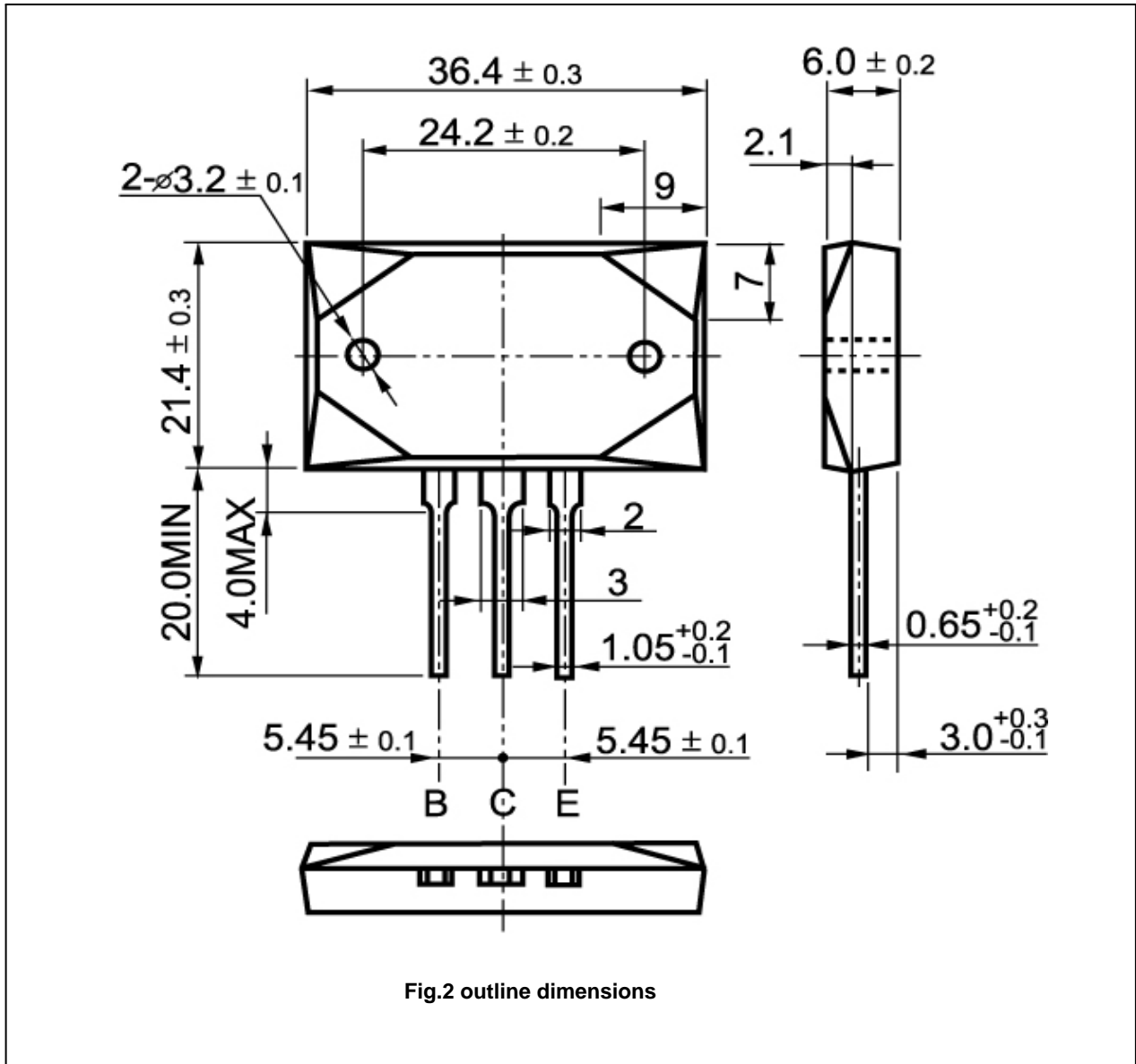


Fig.2 outline dimensions